The listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) An integrated circuit capacitor, comprising:

an electrically insulating electrode support layer having an opening therein, on an integrated circuit substrate;

a U-shaped lower electrode in the opening;

a first capacitor dielectric layer extending on an inner surface and outer portion of the U-shaped lower electrode;

a second capacitor dielectric layer extending between the outer portion of the U-shaped lower electrode and the first capacitor dielectric ~~and also extending,~~ between the outer portion of the U-shaped lower electrode and an inner sidewall of the opening and directly contacting a surface of the first capacitor dielectric layer opposite the U-shaped lower electrode; and

an upper electrode on the first capacitor dielectric layer.

2. (Original) The integrated circuit capacitor of Claim 1, wherein the second capacitor dielectric layer does not extend on the inner surface of the U-shaped lower electrode.

3. (Original) The integrated circuit capacitor of Claim 1, wherein the electrically insulating electrode support layer comprises:

a mold layer on the integrated circuit substrate; and

an etch stop layer on the mold layer.

4. (Original) The integrated circuit capacitor of Claim 3, wherein the mold layer comprises silicon oxide and wherein the etch stop layer comprises at least one of silicon nitride and/or tantalum oxide.

5. (Original) The integrated circuit capacitor of Claim 1, wherein the first capacitor dielectric layer extends onto the support layer.

6. (Original) The integrated circuit capacitor of Claim 1, wherein the first capacitor dielectric layer comprises tantalum oxide, aluminum oxide (Al_2O_3), and/or Hafnium Oxide (HfO_2).

7. (Original) The integrated circuit capacitor of Claim 1, wherein the second capacitor dielectric layer comprises a dielectric material that is not etched by an oxide etchant.

8. (Currently Amended) An integrated circuit capacitor, comprising:

an electrically insulating electrode support layer having an opening therein, on an integrated circuit substrate;

a U-shaped lower electrode in the opening;

a first capacitor dielectric layer extending on an inner surface and outer portion of the U-shaped lower electrode; and

a second capacitor dielectric layer extending between the outer portion of the U-shaped lower electrode and the first capacitor dielectric ~~and also extending,~~ between the outer portion of the U-shaped lower electrode and an inner sidewall of the opening and directly contacting a surface of the first capacitor dielectric layer opposite the U-shaped lower electrode.

Claim 9 (Canceled).

10. (New) The integrated circuit capacitor of Claim 8, wherein the second capacitor dielectric layer does not extend on the inner surface of the U-shaped lower electrode.

11. (New) The integrated circuit capacitor of Claim 8, wherein the electrically insulating electrode support layer comprises:

a mold layer on the integrated circuit substrate; and

an etch stop layer on the mold layer.

12. (New) The integrated circuit capacitor of Claim 11, wherein the mold layer comprises silicon oxide and wherein the etch stop layer comprises at least one of silicon nitride and/or tantalum oxide.

13. (New) The integrated circuit capacitor of Claim 8, wherein the first capacitor dielectric layer extends onto the support layer.

14. (New) The integrated circuit capacitor of Claim 8, wherein the first capacitor dielectric layer comprises tantalum oxide, aluminum oxide (Al_2O_3), and/or Hafnium Oxide (HfO_2).

15. (New) The integrated circuit capacitor of Claim 8, wherein the second capacitor dielectric layer comprises a dielectric material that is not etched by an oxide etchant.